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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	DMA, LCD, WDT
Number of I/O	38
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 6x16b, 4x24b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkm33z128aclh5

- Communication interfaces
  - One SPI module with FIFO support (supports 5V AMR operation)
  - One SPI module without FIFO (no AMR operation)
  - Two I2C modules with SMBus support
  - Two UART modules with ISO7816 support and Two UART without ISO 7816 support
  - Any one SCI can be used for IrDA operation. 5V AMR support on one SCI.

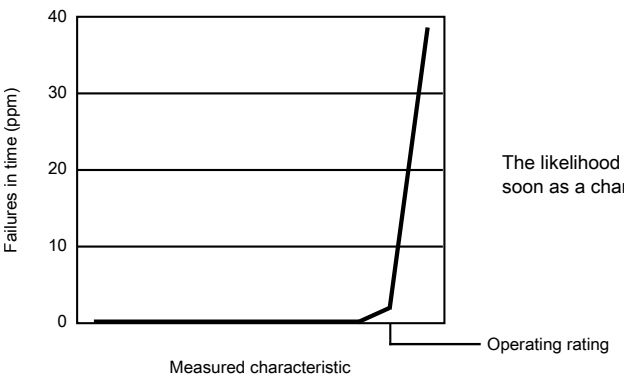
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

3.4.1 Example

This is an example of an operating rating:

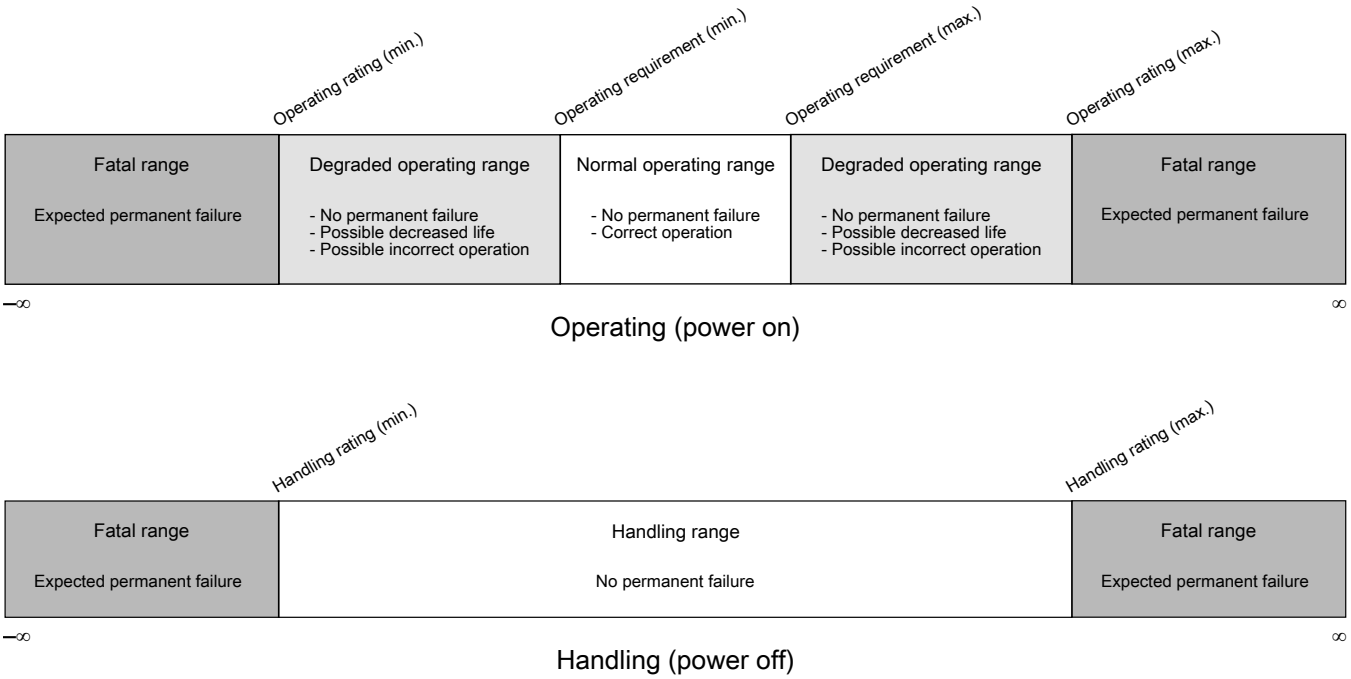
Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	–0.3	1.2	V

3.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

4 Ratings

4.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model (All pins except RESET pin)	-4000	+4000	V	1
	Electrostatic discharge voltage, human body model (RESET pin only)	-2500	+2500	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model (for corner pins)	-750	+750	V	2
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	3
V_{PESD}	Powered ESD voltage	-6000	+6000	V	
I_{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.
3. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.

4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.6	V
V_{DIO}	Digital input voltage (except $\overline{RESET}$, EXTAL, and XTAL)	–0.3	V_{DD} + 0.3	V
$V_{DTamper}$	Tamper input voltage	–0.3	V_{BAT} + 0.3	V
V_{AIO}	Analog[1], $\overline{RESET}$, EXTAL, and XTAL input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V
V_{BAT}	RTC battery supply voltage	–0.3	3.6	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5 General

5.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

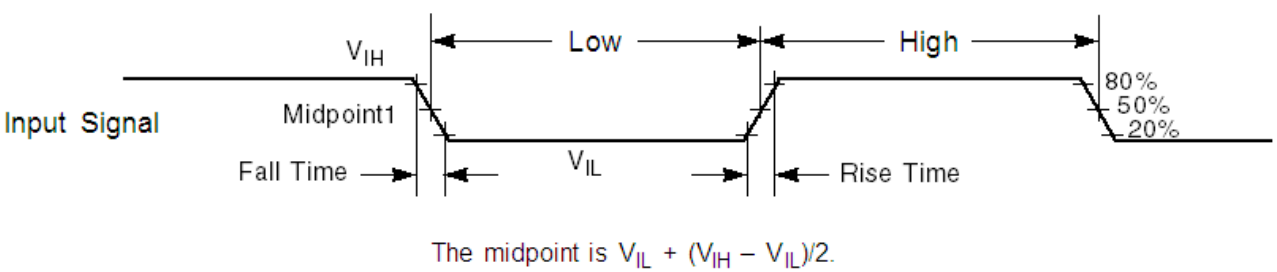


Figure 1. Input signal measurement reference

5.2 Nonswitching electrical specifications

5.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage when AFE is operational	2.7	3.6	V	
	Supply voltage when AFE is NOT operational	1.71	3.6	V	
V_{DDA}	Analog supply voltage	2.7	3.6	V	
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	–0.1	0.1	V	
$V_{SS} – V_{SSA}$	V_{SS}-to-V_{SSA} differential voltage	–0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	1
V_{IH}	Input high voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	 0.7 × V_{DD} 0.75 × V_{DD}	 — —	 V V	
V_{IL}	Input low voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	 — —	 0.35 × V_{DD} 0.3 × V_{DD}	 V V	
V_{HYS}	Input hysteresis	0.06 × V_{DD}	—	V	
I_{ICDIO}	Digital pin negative DC injection current — single pin • V_{IN} < V_{SS}-0.3V	-5	—	mA	
I_{ICAIO}	Analog[2], EXTAL, and XTAL pin DC injection current — single pin • V_{IN} < V_{SS}-0.3V (Negative current injection) • V_{IN} > V_{DD}+0.3V (Positive current injection)	 -3 —	 — +3	mA	
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection • Positive current injection	 -25 —	 — +25	mA	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. V_{BAT} always needs to be there for the chip to be operational.
2. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	

Table continues on the next page...

Table 4. Voltage and current operating behaviors (continued)

Symbol	Description	Min.	Max.	Unit	Notes
V_{OL}	Output low voltage — high-drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 20 mA	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 10 mA	—	0.5	V	
	Output low voltage — low-drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 5 mA	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 2.5 mA	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	100	mA	
I_{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	µA	
R_{PU}	Internal pullup resistors	30	60	kΩ	1,
R_{PD}	Internal pulldown resistors	30	60	kΩ	2

1. Measured at Vinput = V_{SS}
2. Measured at Vinput = V_{DD}

5.2.4 Power mode transition operating behaviors

All specifications except t_{POR}, and VLLSx→RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 50 MHz
- Bus clock = 25 MHz
- Flash clock = 25 MHz
- Temp: -40 °C, 25 °C, and 85 °C
- V_{DD}: 1.71 V, 3.3 V, and 3.6 V

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execute the first instruction across the operating temperature range of the chip.	563	659	µs	1
	• VLLS0 → RUN	—	372	µs	
	• VLLS1 → RUN	—	372	µs	
	• VLLS2 → RUN	—	273	µs	
	• VLLS3 → RUN	—	273	µs	
	• VLPS → RUN	—	5.0	µs	

Table continues on the next page...

5.4.2 Thermal attributes

Board type	Symbol	Description	100 LQFP	44 LGA	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	63	95	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	50	50	°C/W	1
Single-layer (1s)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	53	79	°C/W	1
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./ min. air speed)	44	45	°C/W	1
—	$R_{\theta JB}$	Thermal resistance, junction to board	36	35	°C/W	2
—	$R_{\theta JC}$	Thermal resistance, junction to case	18	28	°C/W	3
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	3	4	°C/W	4

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)*.
2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*.
3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
4. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.

6 Peripheral operating requirements and behaviors

6.1 Core modules

6.1.1 Single Wire Debug (SWD)

Table 12. SWD switching characteristics at 2.7 V (2.7-3.6 V)

Symbol	Description	Value	Unit	Notes
SWD CLK	Frequency of SWD operation	20	MHz	1
Inputs, tSUI	Data setup time	5	ns	1
inputs,tHI	Data hold time	0	ns	1
after clock edge, tDVO	Data valid Time	32	ns	1
tHO	Data Valid Hold	0	ns	1

1. Input transition assumed =1 ns. Output transition assumed = 50 pf.

Table 13. Switching characteristics at 1.7 V (1.7-3.6 V)

Symbol	Description	Value	Unit	Notes
SWD CLK	Frequency of SWD operation	18	MHz	
Inputs, tSUI	Data setup time	4.7	ns	
inputs,tHI	Data hold time	0	ns	
after clock edge, tDVO	Data valid Time	49.4	ns	2
tHO	Data Valid Hold	0	ns	

1. Frequency of SWD clock (18 Mhz) is applicable only in case the input setup time of the device outside is not more than 6.15 ns, else the frequency of SWD clock would need to be lowered.

6.1.2 Analog Front End (AFE)

AFE switching characteristics at (2.7 V-3.6 V)

Case1: Clock is coming In and Data is also coming In (XBAR ports timed with respect to the XBAR ports timed with respect to AFE clock defined at pad ptb[7] and pte[3])

Table 14. AFE switching characteristics (2.7 V-3.6 V)

Symbol	Description	Value	Unit	Notes
AFE CLK	Frequency of operation	10	MHz	1
Inputs, tSUI	Data setup time	5	ns	1
inputs,tHI	Data hold time	0	ns	1

1. Input Transition: 1ns. Output Load: 50 pf.

6.2.2 Oscillator electrical specifications

6.2.2.1 Oscillator DC electrical specifications

Table 19. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	
I_{DDOSC}	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	—	500	—	nA	
	• 1 MHz	—	200	—	µA	
	• 4 MHz	—	200	—	µA	
	• 8 MHz (RANGE=01)	—	300	—	µA	
	• 16 MHz	—	950	—	µA	
	• 24 MHz	—	1.2	—	mA	
	• 32 MHz	—	1.5	—	mA	
I_{DDOSC}	Supply current — high-gain mode (HGO=1)					1
	• 32 kHz	—	25	—	µA	
	• 1 MHz	—	300	—	µA	
	• 4 MHz	—	400	—	µA	
	• 8 MHz (RANGE=01)	—	500	—	µA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
C_x	EXTAL load capacitance	—	—	—		2, 3
C_y	XTAL load capacitance	—	—	—		2, 3
Capacitance of EXTAL • Die level (100 LQFP) • Package level (100 LQFP)	247 0.495	—	—	ff pF		
	Capacitance of XTAL • Die level (100 LQFP) • Package level (100 LQFP)	265 0.495	—	—	ff pF	

Table continues on the next page...

6.2.2.2 Oscillator frequency specifications

Table 20. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low-frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
$f_{osc\_hi\_1}$	Oscillator crystal or resonator frequency — high-frequency mode (low range) (MCG_C2[RANGE]=01)	1	—	8	MHz	
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	48	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—		—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—		—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.
2. When transitioning from FEI or FBI to FBE mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
3. Proper PC board layout procedures must be followed to achieve specifications.
4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

6.2.3 32 kHz oscillator electrical characteristics

6.2.3.1 32 kHz oscillator DC electrical specifications

Table 21. 32kHz oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{BAT}	Supply voltage	1.71	—	3.6	V
R_F	Internal feedback resistor	—	100	—	MΩ
C_{para}	Parasitical capacitance of EXTAL32 and XTAL32	—	5	7	pF
V_{pp}[1]	Peak-to-peak amplitude of oscillation	—	0.6	—	V

1. When a crystal is being used with the 32 kHz oscillator, the EXTAL32 and XTAL32 pins should only be connected to required oscillator components and must not be connected to any other devices.

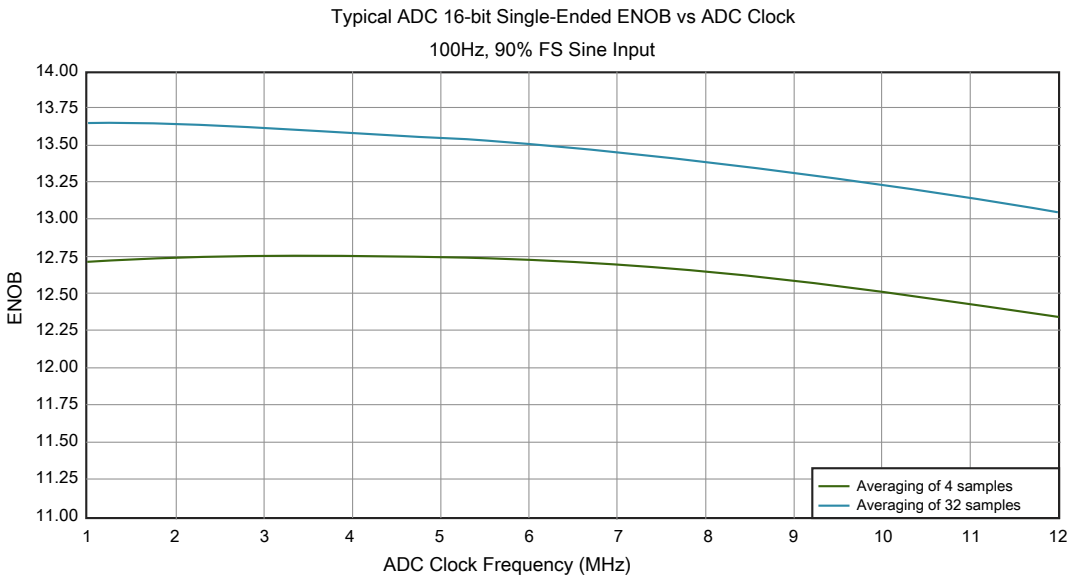


Figure 3. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

6.4.2 CMP and 6-bit DAC electrical specifications

Table 29. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	µA
I_{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	µA
V_{AIN}	Analog input voltage	V_{SS} – 0.3	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis[1] • CR0[HYSTCTR] = 00 • CR0[HYSTCTR] = 01 • CR0[HYSTCTR] = 10 • CR0[HYSTCTR] = 11	— — — —	5 10 20 30	— — — —	mV mV mV mV
V_{CMPOh}	Output high	V_{DD} – 0.5	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	µs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	µA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

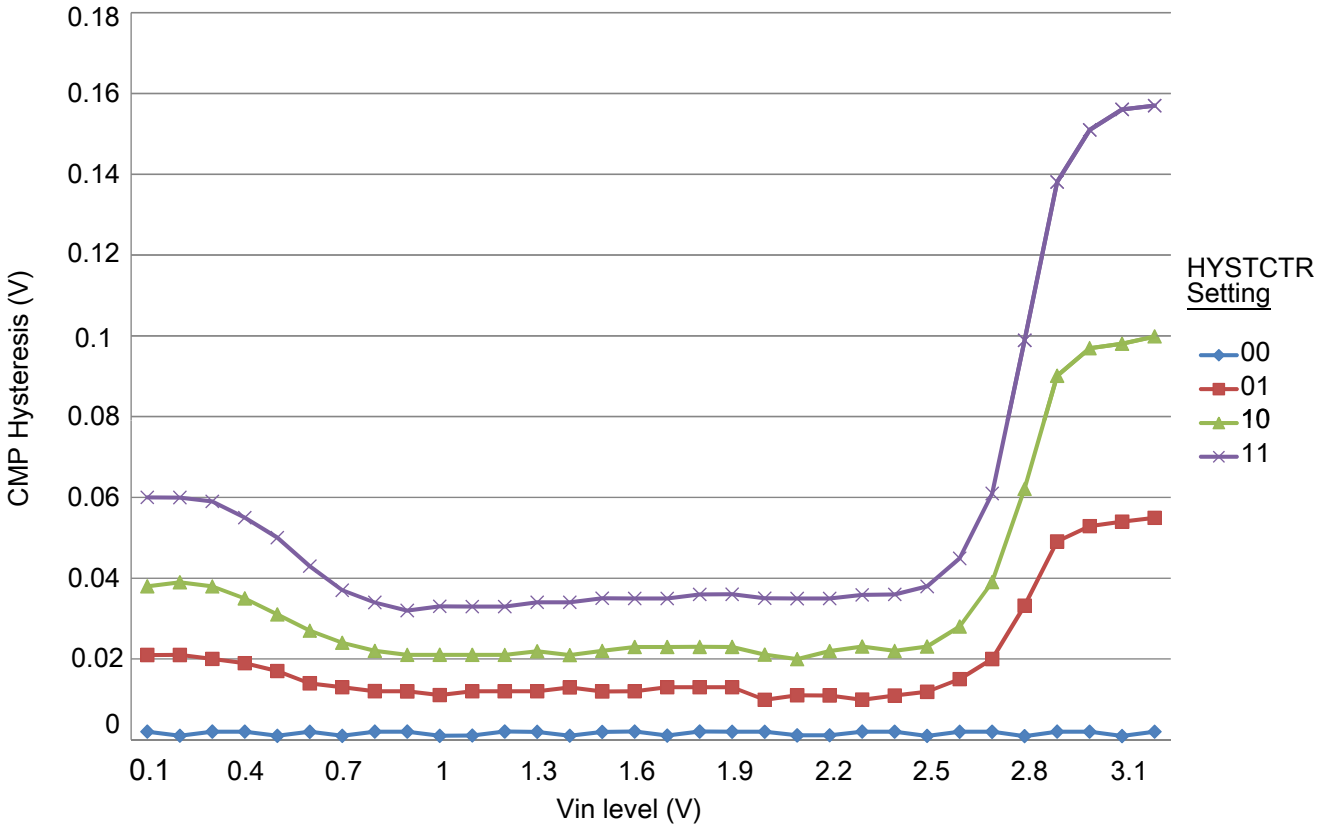


Figure 5. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

6.4.3 Voltage reference electrical specifications

Table 30. 1.2 VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71[1]	3.6	V	
T_A	Temperature	–40	85	°C	
C_L	Output load capacitance	100		nF	2, 3

1. AFE is enabled.
2. C_L must be connected between VREFH and VREFL.
3. The load capacitance should not exceed ±25% of the nominal specified C_L value over the operating temperature range of the device.

Table 31. VREF full-range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
VREFH	Voltage reference output with factory trim at nominal V_{DDA} and temperature = 25 °C	1.1915	1.195	1.2027	V	

Table continues on the next page...

Table 31. VREF full-range operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
VREFH	Voltage reference output with — factory trim	1.1584	—	1.2376	V	
VREFH	Voltage reference output — user trim	1.178	—	1.202	V	
VREFL	Voltage reference output	0.38	0.4	0.42	V	
V_{step}	Voltage reference trim step	—	0.5	—	mV	
V_{tdrift}	Temperature drift when ICOMP = 0 across full temperature range	—	18	—	ppm/ºC	
	Temperature drift when ICOMP = 1 across full temperature range	—	10	—	ppm/°C	1
	Temperature drift when ICOMP = 1 across -40 ºC to 70 ºC	—	9	—	ppm/°C	1, 2
	Temperature drift when ICOMP = 1 across 0 ºC to 50 ºC	—	9	—	ppm/°C	1, 2
Ac	Aging coefficient	—	—	400	uV/yr	
I_{bg}	Bandgap only current	—	—	80	µA	2
I_{lp}	Low-power buffer current	—	—	0.19	µA	2
I_{hp}	High-power buffer current	—	—	0.5	mA	2
I_{LOAD}	VREF buffer current	—	—	1	mA	3
ΔV_{LOAD}	Load regulation • current = + 1.0 mA • current = - 1.0 mA	—	 2 5	—	mV	2, 4
T_{stup}	Buffer startup time	—	—	20	ms	
V_{vdrift}	Voltage drift (VREFHmax -VREFHmin across the full voltage range)	—	0.5	—	mV	2

1. ICOMP=1 is recommended to get best temperature drift. CHOPEN bit = 1 is also recommended.
2. See the chip's Reference Manual for the appropriate settings of VREF Status and Control register.
3. See the chip's Reference Manual for the appropriate settings of SIM Miscellaneous Control Register.
4. Load regulation voltage is the difference between VREFH voltage with no load vs. voltage with defined load.

NOTE

Temperature drift per degree is ((VREFHmax-VREFHmin)/ (temperature range)/VREFHmin) in ppm/ºC

Table 32. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_A	Temperature	0	50	°C	

Table 34. ΣΔ ADC + PGA specifications (continued)

Symbol	Description	Conditions	Min	Typ[1]	Max	Unit	Notes
SNR	Signal to Noise Ratio	Normal Mode • f_{IN}=50Hz; gain=01, common mode=0V, V_{pp}=1000mV (full range diff.) • f_{IN}=50Hz; gain=02, common mode=0V, V_{pp}= 500mV (differential ended) • f_{IN}=50Hz; gain=04, common mode=0V, V_{pp}= 250mV (differential ended) • f_{IN}=50Hz; gain=08, common mode=0V, V_{pp}= 125mV (differential ended) • f_{IN}=50Hz; gain=16, common mode=0V, V_{pp}= 62mV (differential ended) • f_{IN}=50Hz; gain=32, common mode=0V, V_{pp}= 31mV (differential ended)	90 88 82 76 70 64	92 90 86 82 78 74		dB	
		Low-Power Mode • f_{IN}=50Hz; gain=01, common mode=0V, V_{pp}=1000mV (full range diff.) • f_{IN}=50Hz; gain=02, common mode=0V, V_{pp}= 500mV (differential ended) • f_{IN}=50Hz; gain=04, common mode=0V, V_{pp}= 250mV (differential ended) • f_{IN}=50Hz; gain=08, common mode=0V, V_{pp}= 125mV (differential ended) • f_{IN}=50Hz; gain=16, common mode=0V, V_{pp}= 62mV (differential ended) • f_{IN}=50Hz; gain=32, common mode=0V, V_{pp}= 31mV (differential ended)	82 76 70 64 58 52	82 78 74 70 66 62		dB	
SINAD	Signal-to-Noise + Distortion Ratio	Normal Mode • f_{IN}=50Hz; gain=01, common mode=0V, V_{pp}=500mV (differential ended)		78		dB	
		Low-Power Mode • f_{IN}=50Hz; gain=01, common mode=0V, V_{pp}=500mV (differential ended)		74		dB	
CMMR	Common Mode Rejection Ratio	• f_{IN}=50Hz; gain=01, common mode=0V, Vid=100 mV • f_{IN}=50Hz; gain=32, common mode=0V, V_{id}=100 mV		70 70		dB	

Table continues on the next page...

Table 34. ΣΔ ADC + PGA specifications (continued)

Symbol	Description	Conditions	Min	Typ[1]	Max	Unit	Notes
E_{offset}	Offset Error	Gain=01, V_{pp}=1000 mV (full range diff.)			+/- 5	mV	
$\Delta Offset_{Temp}$	Offset Temperature Drift[3]	Gain=01, V_{pp}=1000mV (full range diff.)			+/- 25	ppm/°C	
$\Delta Gain_{Temp}$	Gain Temperate Drift - Gain error caused by temperature drifts[4]	• Gain=01, V_{pp}=500mV (differential ended) • Gain=32, V_{pp}=15mV (differential ended)			+/- 75	ppm/°C	
$PSRR_{AC}$	AC Power Supply Rejection Ratio	Gain=01, VCC = 3V ± 100mV, f_{IN} = 50 Hz		60		dB	
XT	Crosstalk (with the input of the affected channel grounded)	Gain=01, V_{id} = 500 mV, f_{IN} = 50 Hz			-100	dB	
f_{MCLK}	Modulator Clock Frequency Range	Normal Mode Low-Power Mode	0.03 0.03		6.5 1.6	MHz	
I_{DDA_PGA}	Current consumption by PGA (each channel)	Normal Mode (f_{MCLK} = 6.144 MHz, OSR= 2048) Low-Power Mode (f_{MCLK} = 0.768MHz, OSR= 256)			2.6 0	mA	5
I_{DDA_ADC}	Current Consumption by ADC (each chanel)	Normal Mode (f_{MCLK} = 6.144 MHz, OSR= 2048) Low-Power Mode (f_{MCLK} = 0.768MHz, OSR= 256)			1.4 0.5	mA	
R_{as}	Equivalent input impedance per single channel	PGA enabled		8		kΩ	

1. Typical values assume VDDA = 3.0 V, Temp = 25°C, f_{MCLK} = 6.144 MHz, OSR = 2048 for Normal mode and f_{MCLK} = 768 kHz, OSR = 256 for Low-Power Mode unless otherwise stated. Typical values are for reference only and are not tested in production.
2. The full-scale input range in single-ended mode is 0.5Vpp
3. Represents combined offset temperature drift of the PGA, SD ADC and Internal 1.2 VREF blocks; Defined by shorting both differential inputs to ground.
4. Represents combined gain temperature drift of the PGA, SD ADC and Internal 1.2 VREF blocks.
5. PGA is disabled in low-power modes.

6.4.4.2 ΣΔ ADC Standalone specifications

Table 35. ΣΔ ADC standalone specifications

Symbol	Description	Conditions	Min	Typ[1]	Max	Unit	Notes
f_{Nyq}	Input bandwidth	Normal Mode Low-Power Mode	1.5 1.5	1.5 1.5	1.5 1.5	kHz	
V_{CM}	Input Common Mode Reference		0		0.8	V	

Table continues on the next page...

6.6.3 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following table provides some reference values to be met on SoC.

Table 36. SPI switching characteristics at 2.7 V (2.7 - 3.6)

Description	Min.	Max.	Unit	Notes
Frequency of operation (F_{sys})	—	50	MHz	1
SCK frequency • Master • Slave	2	12.5 12.5	MHz Mhz	3
SCK Duty Cycle	50%	—	—	
Data Setup Time (inputs, tSUI) • Master • Slave	25 3		ns	
Input Data Hold Time (inputs, tHI) • Master • Slave	0 1		ns	
Data hold time (outputs, tHO) • Master • Slave	0 0		ns	
Data Valid Out Time (after SCK edge, tDVO) • Master • Slave	13 28		ns	
Rise time input • Master • Slave	1 1		ns	
Fall time input • Master • Slave	1 1		ns	
Rise time output • Master • Slave	8.9 8.9		ns	
Fall time output • Master • Slave	7.8 7.8		ns	

1. SPI modules will work on core clock.
2. F_{sys}/(Max Divider Value from registers)
3. F_{SYS}/2 in Master mode and F_{SYS}/4 in Slave mode. F_{SYS}/4 in Master as well as Slave Modes, where F_{SYS}=50Mhz

NOTE

The values assumed for input transition and output load are:
Input transition = 1 ns Output load = 50 pF

Table 37. SPI switching characteristics at 1.7 V (1.7 - 3.6)

Description	Min.	Max.	Unit	Notes
Frequency of operation (F_{sys})	—	50	MHz	

Table continues on the next page...

Table 38. SPI switching characteristics at 1.7 V (1.7 - 3.6) (continued)

Description	Min.	Max.	Unit	Notes
Rise time input • Master • Slave	 1 1		ns	
Fall time input • Master • Slave	 1 1		ns	
Rise time output • Master • Slave	 30.4 30.4		ns	
Fall time output • Master • Slave	 33.5 29.0		ns	

Table 39. SPI switching characteristics at 2.7 V (2.7 - 3.6)

Description	Min.	Max.	Unit	Notes
Data Setup Time (inputs, tSUI) • Master • Slave	 29 4		ns	
Input Data Hold Time (inputs, tHI) • Master • Slave	 0 1		ns	
Data hold time (outputs, tHO) • Master • Slave	 0 0		ns	
Data Valid Out Time (after SCK edge, tDVO) • Master • Slave	 49 49		ns	
Rise time input • Master • Slave	 1 1		ns	
Fall time input • Master • Slave	 1 1		ns	
Rise time output • Master • Slave	 17.3 17.3		ns	
Fall time output • Master • Slave	 16.6 16.0		ns	

6.7 Human-Machine Interfaces (HMI)

8.3.1 100-pin LQFP

Figure below shows the KM 100 LQFP pinouts.

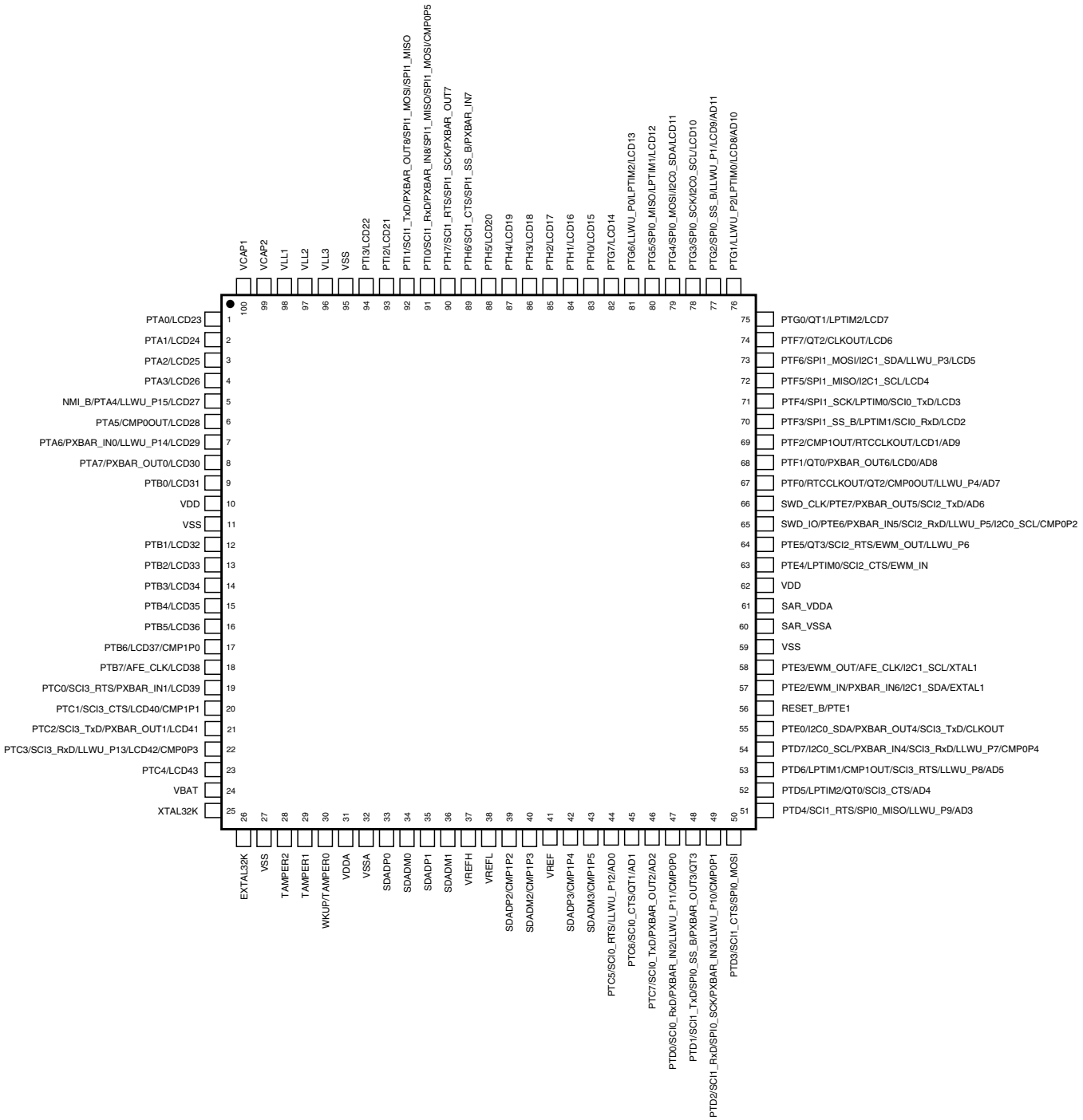


Figure 6. 100-pin LQFP Pinout Diagram

8.3.3 44-pin LGA

Figure below shows the 44-pin LGA pinouts.

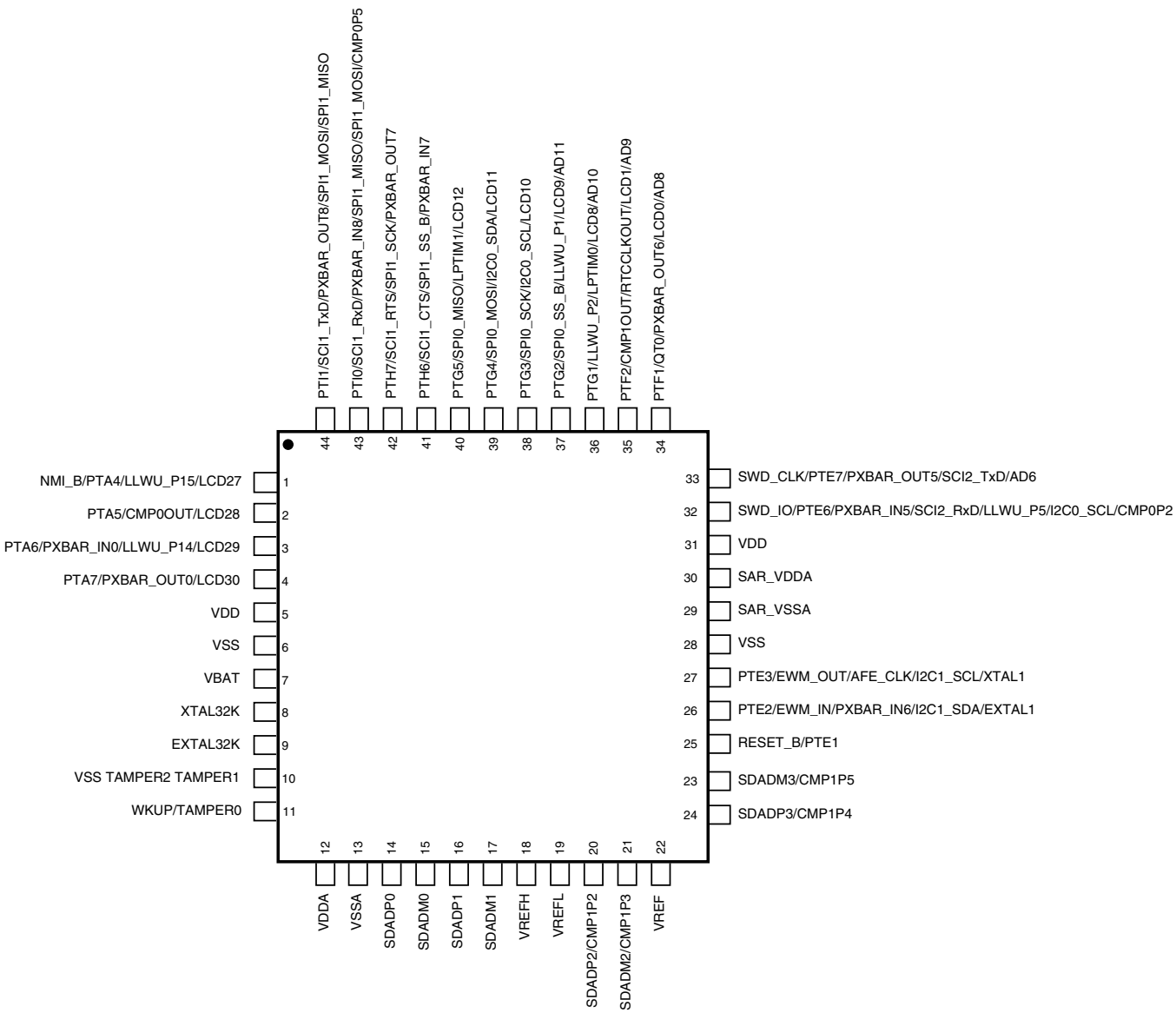


Figure 8. 44-pin LGA Pinout Diagram

NOTE

VSS also connects to flag on 44 LGA.